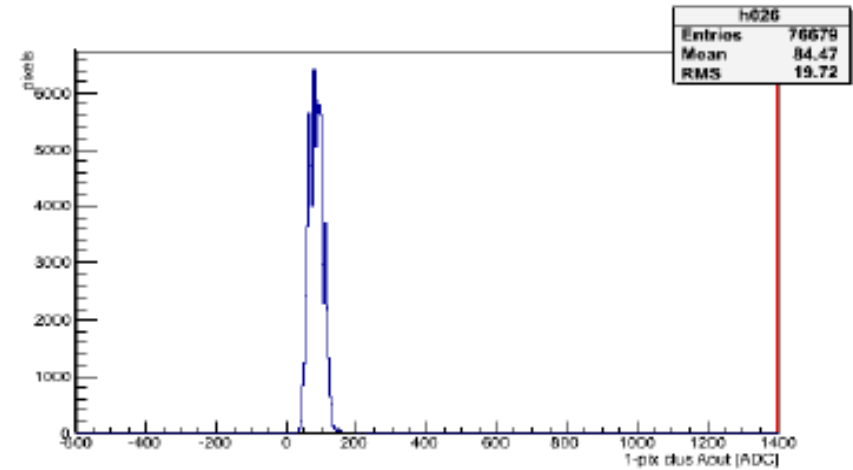
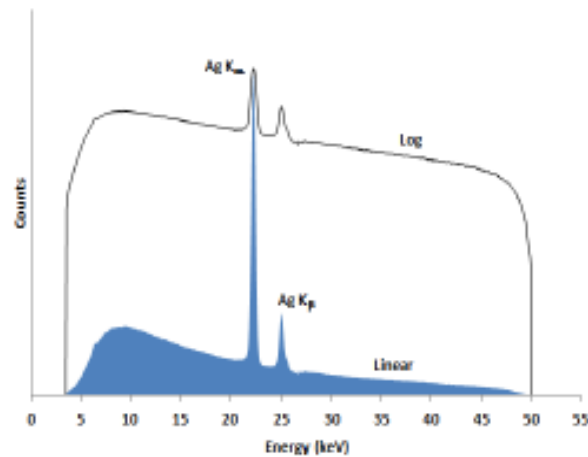


- X-Ray Calibration of digital irradiated Chips
(Tobias Lapsien)
- IV/CV Measurements of the remaining Wafers

Matteo Centis Vignali, Erika Garutti, Johannes Haller, Malte Hoffmann, Tobias Lapsien, Stefan Mättig, Jennifer Sibille, Valentina Sola, Georg Steinbrück

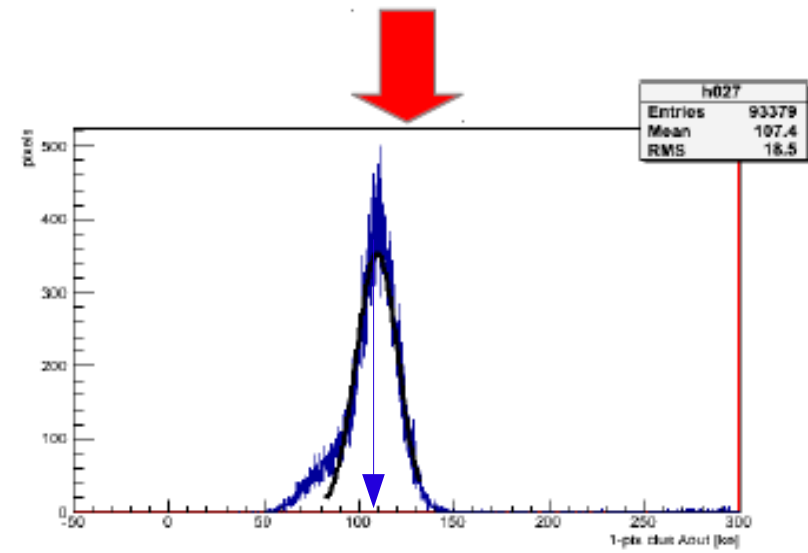
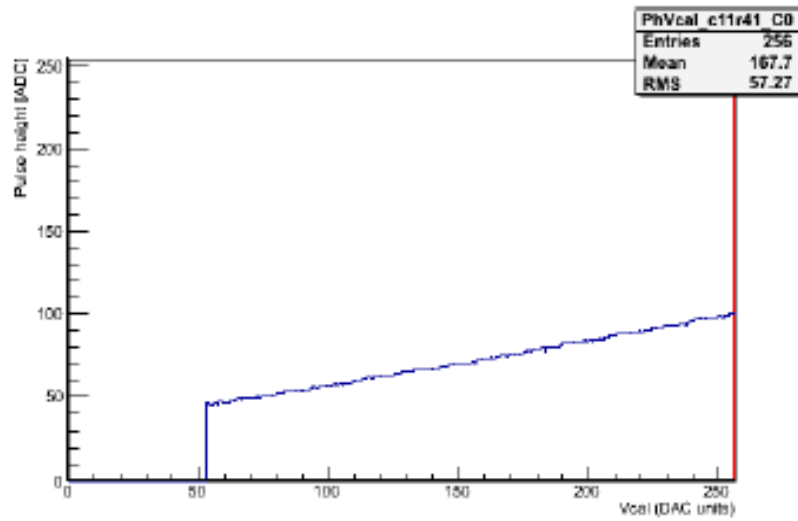
The Spectrum Method

Mini-X Silver (Ag) X-Ray Tube Output Spectrum



Choose specific energy with different targets

Measure ph-spectrum
in adc units

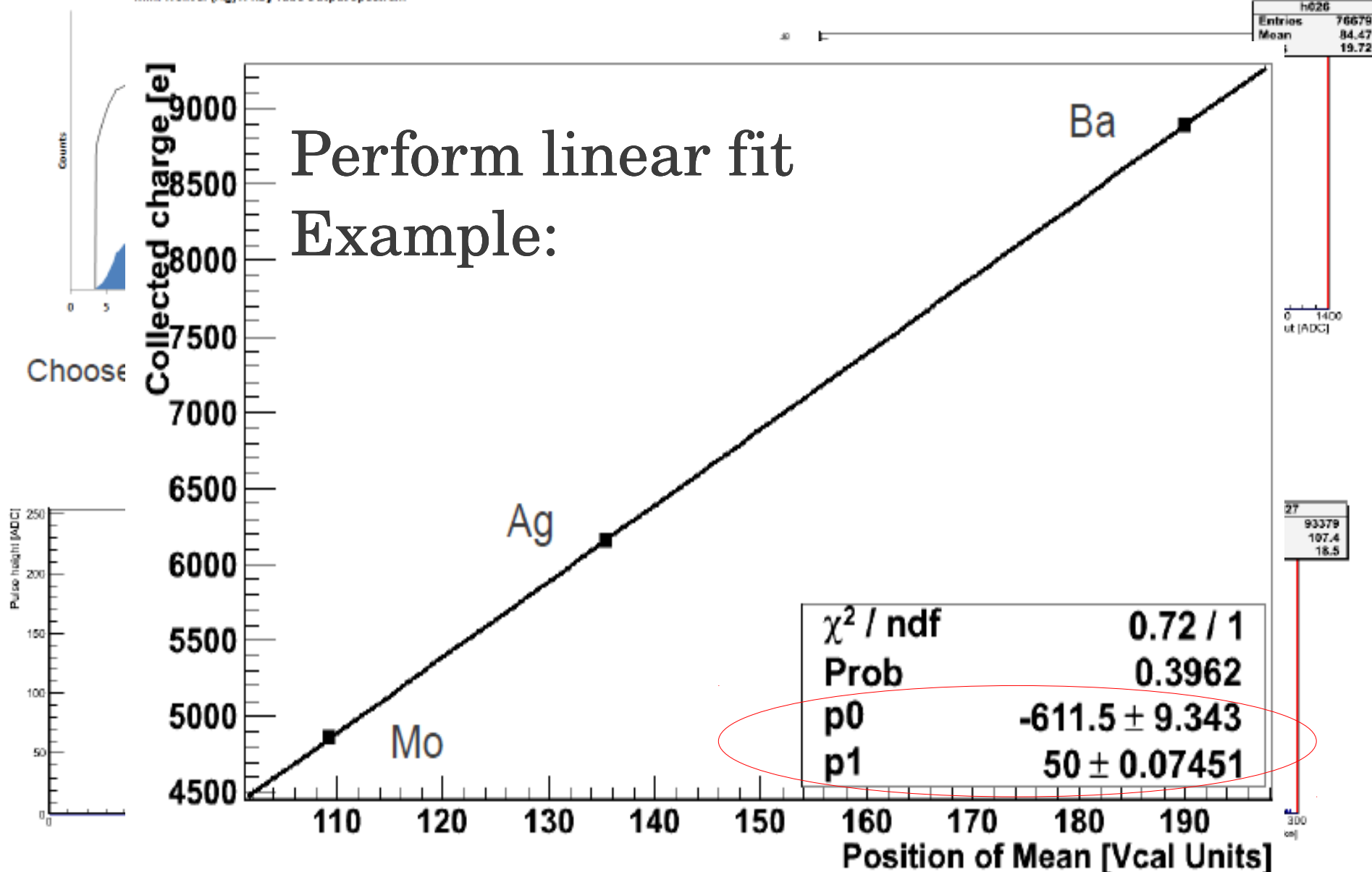


Do ph-calibration

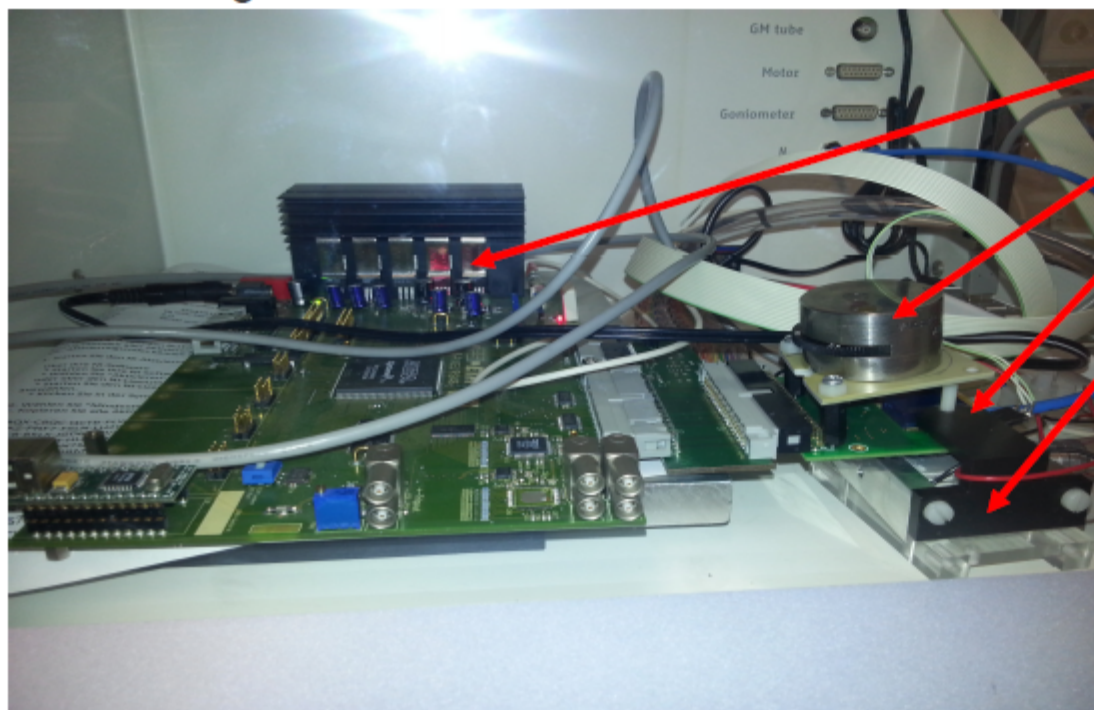
Get ph-distribution in vcal units

The Spectrum Method

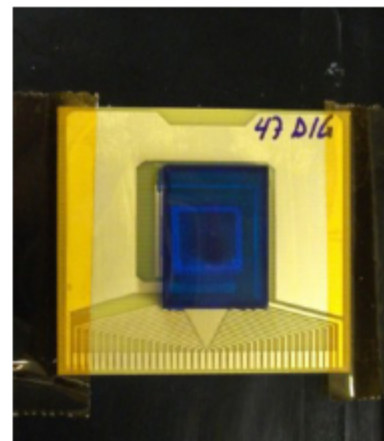
Mini-X Silver (Ag) X-Ray Tube Output Spectrum



Measurement Setup



Testboard
Variable X-ray source
Digital single chip
Cold block with peltiers



• Bias-voltage
= 200V

• **3 targets were used:**

Mo: 17.48 keV (4.9 ke in Si)
Ag: 22.16 keV (6.2 ke in Si)
Ba: 32.19 keV (8.9 ke in Si)

Chip 202 (0.9×10^{14} p/cm²; 3Mrad)

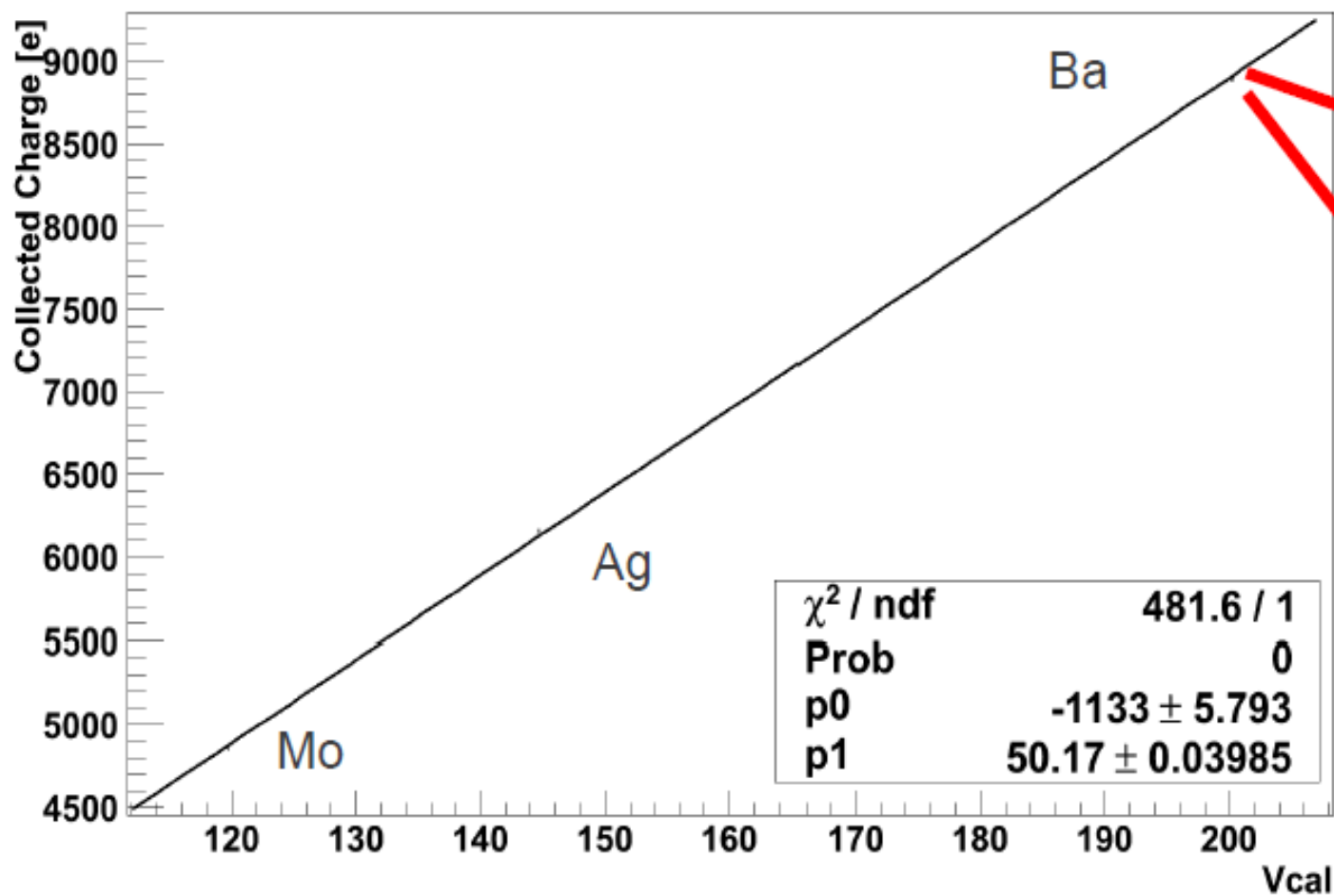
Calibrated at: -15° (Thr1= 35VCAL, Thr2= 50VCAL)
+15° (Thr1= 35VCAL)

Chip 203 (4×10^{14} p/cm²; 13Mrad)

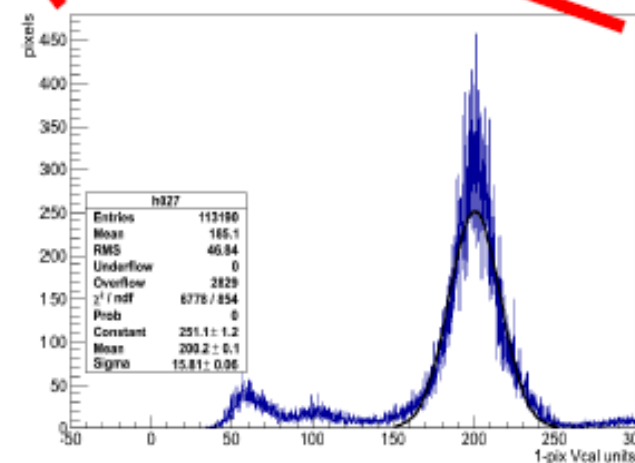
Calibrated at: -15° (Thr1= 35VCAL)

Chip 202: $T = -15^\circ$, $\text{Thr} = 35\text{Vcal}$

Chip202, -15C, Thr=35Vcal

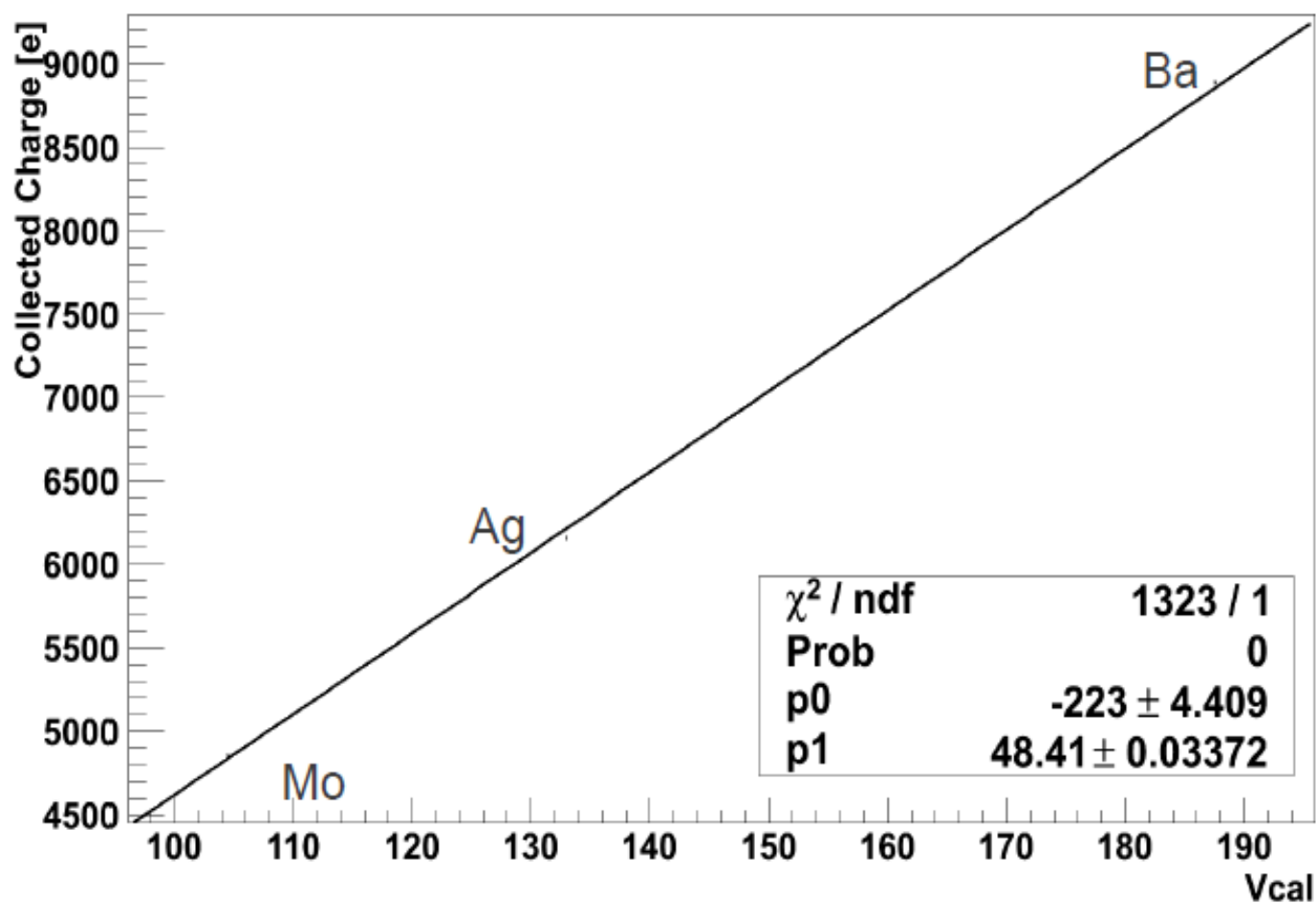


- Calibration done with a threshold of 35Vcal
- Leakage current: 25uA



Chip 202: $T=-15^{\circ}$, $\text{Thr}= 50\text{Vcal}$

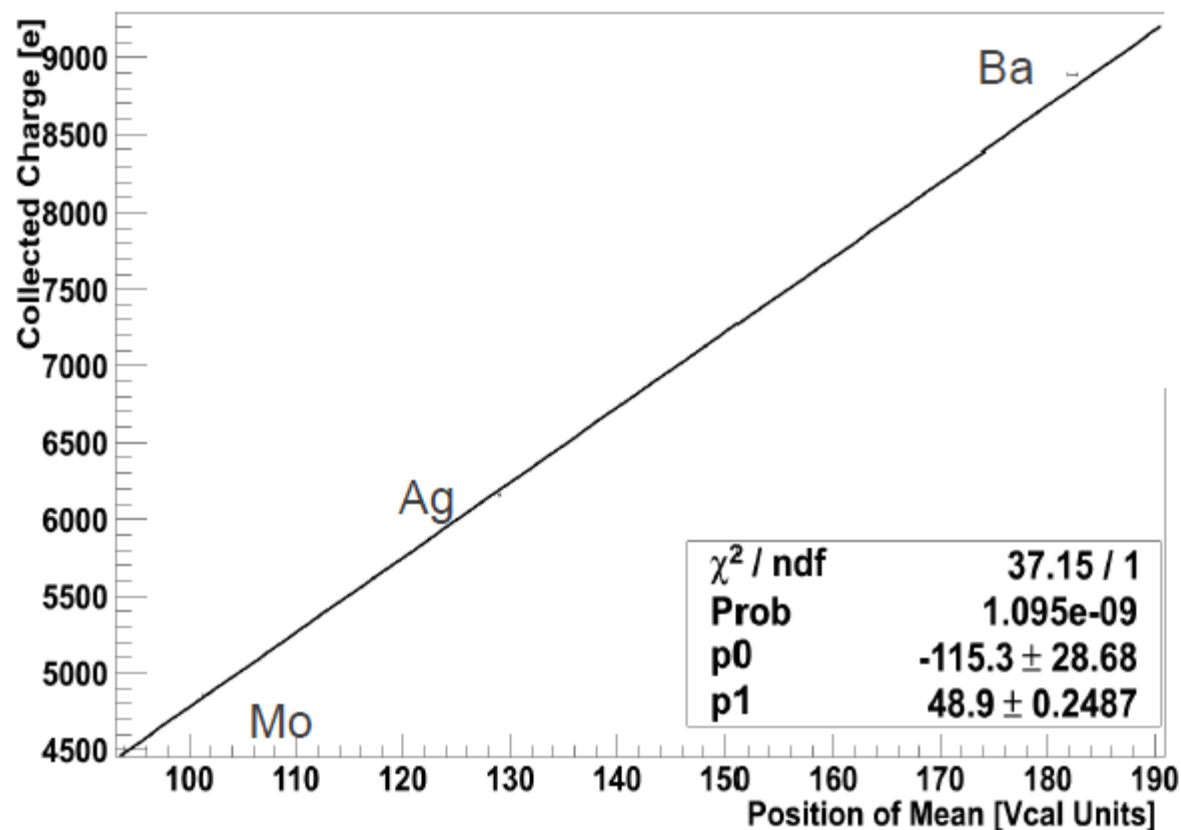
Chip202, -15C, Thr=50Vcal



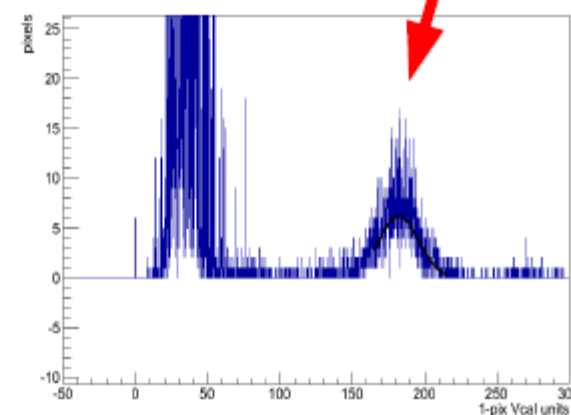
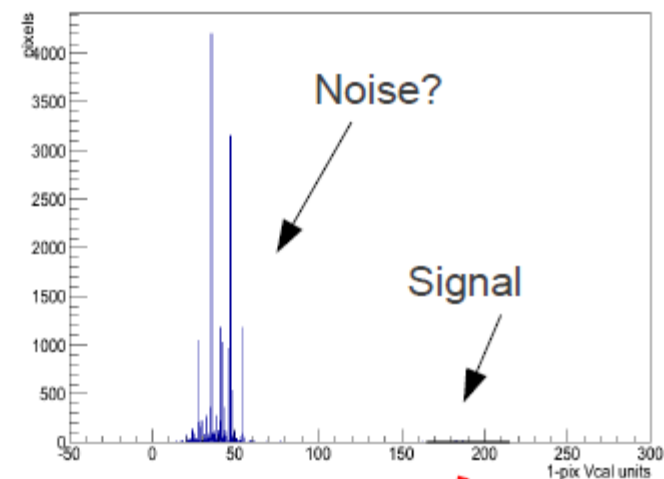
- Calibration done with threshold of 50Vcal units
- Leakage current: 25uA

Chip 202: $T=15^\circ$, $\text{Thr}= 35\text{Vcal}$

Chip202, $T=15\text{C}$, $\text{Thr}=35\text{Vcal}$

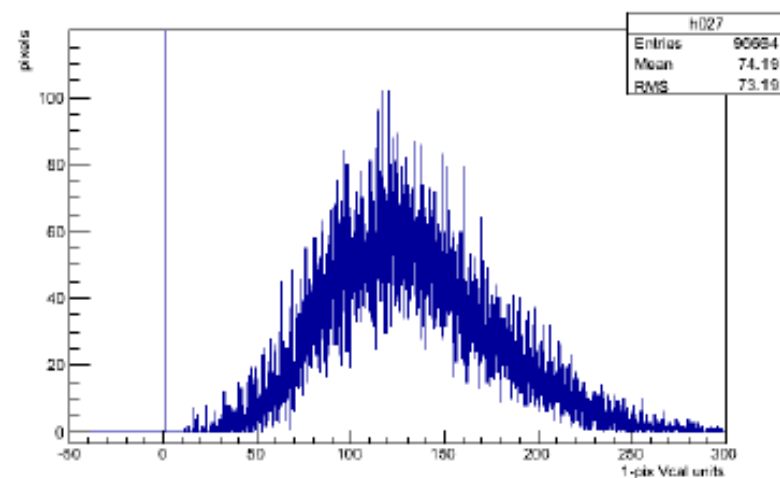
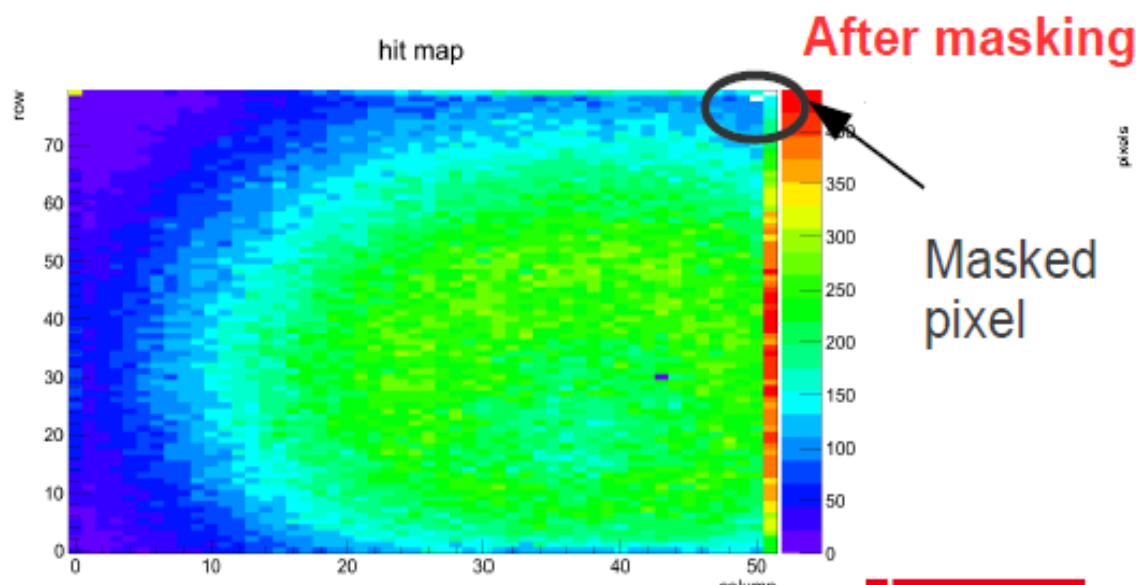
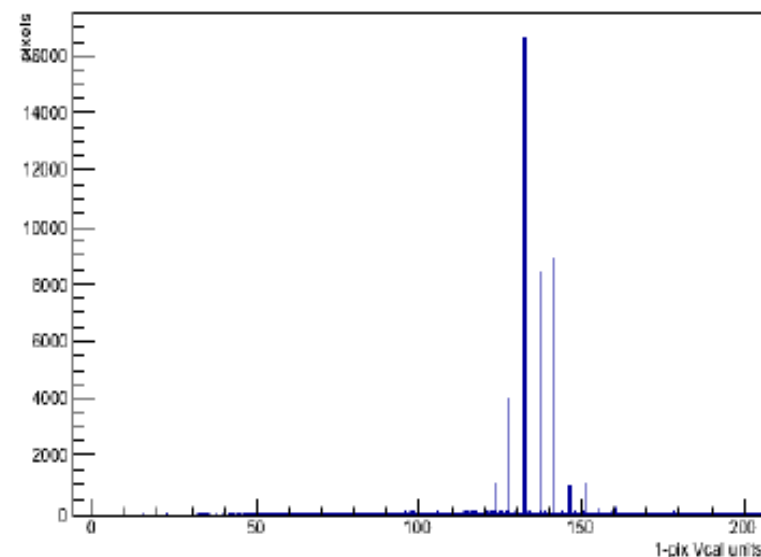
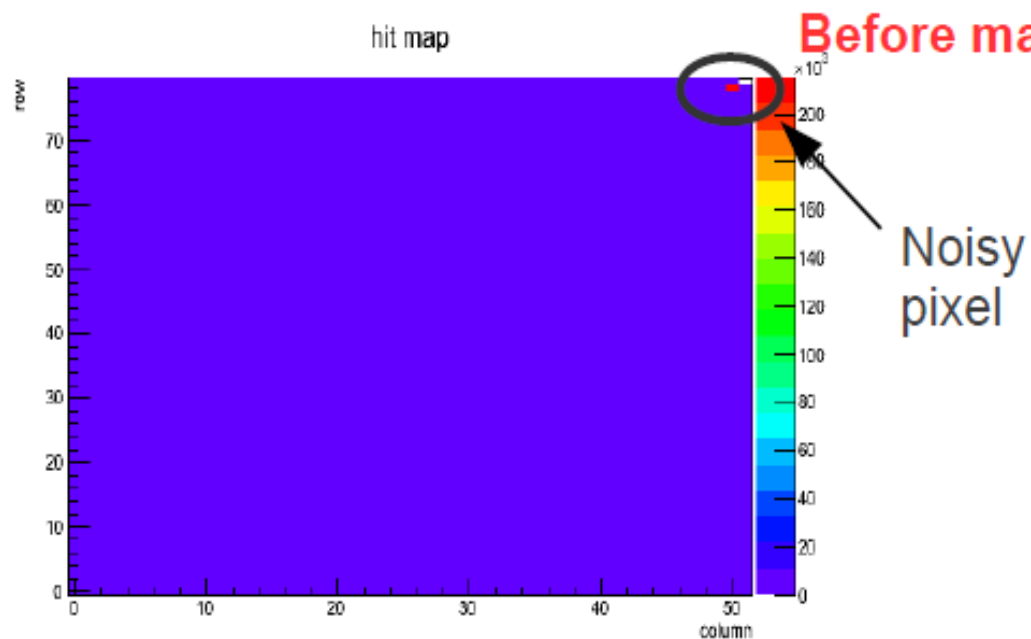


Threshold 35Vcal



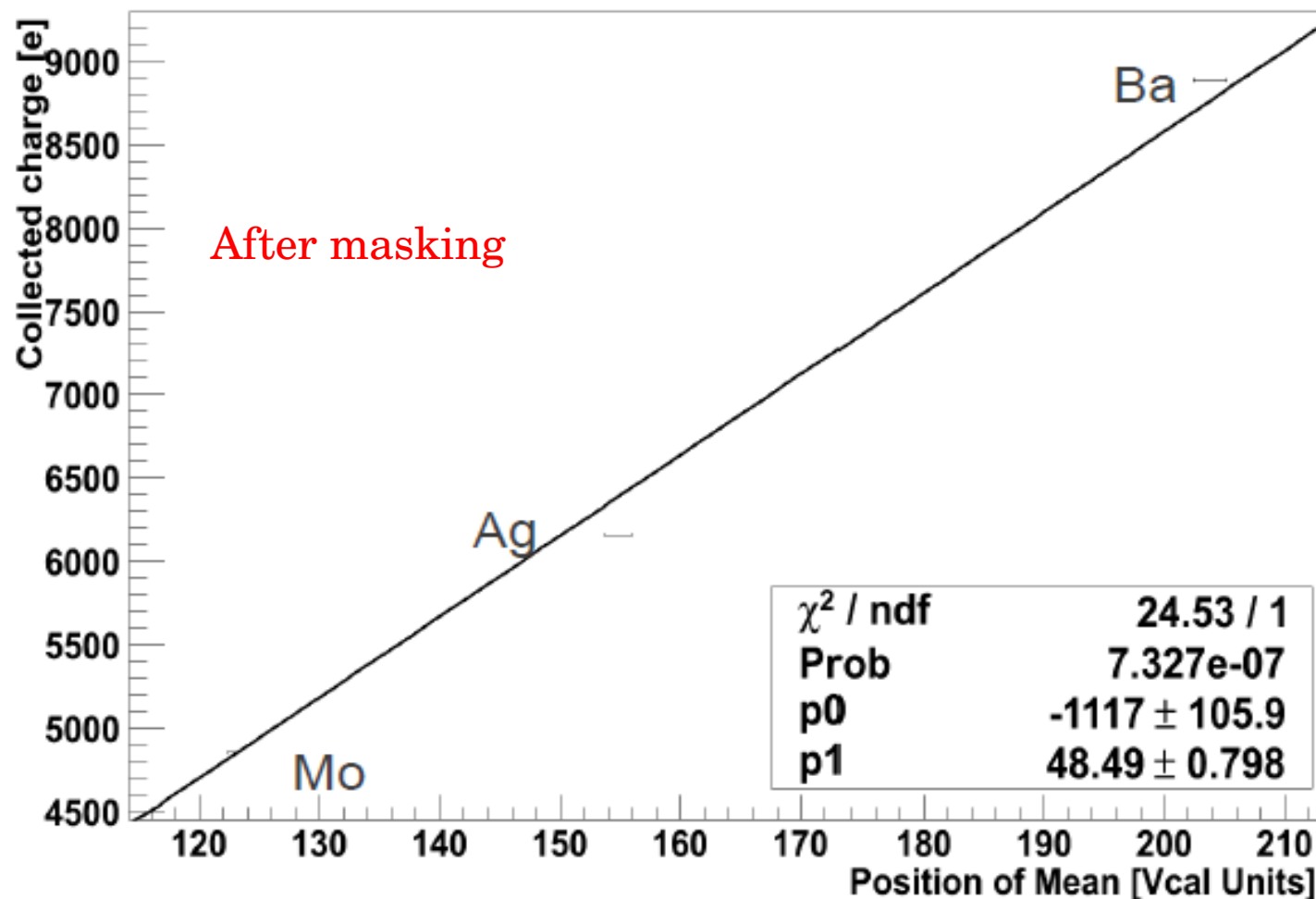
Leakage current much higher: 130uA

Chip 203: $T = -15^\circ$, $\text{Thr} = 35 \text{VCAL}$



Chip 203: $T = -15^\circ$, $\text{Thr} = 35 \text{ VCAL}$

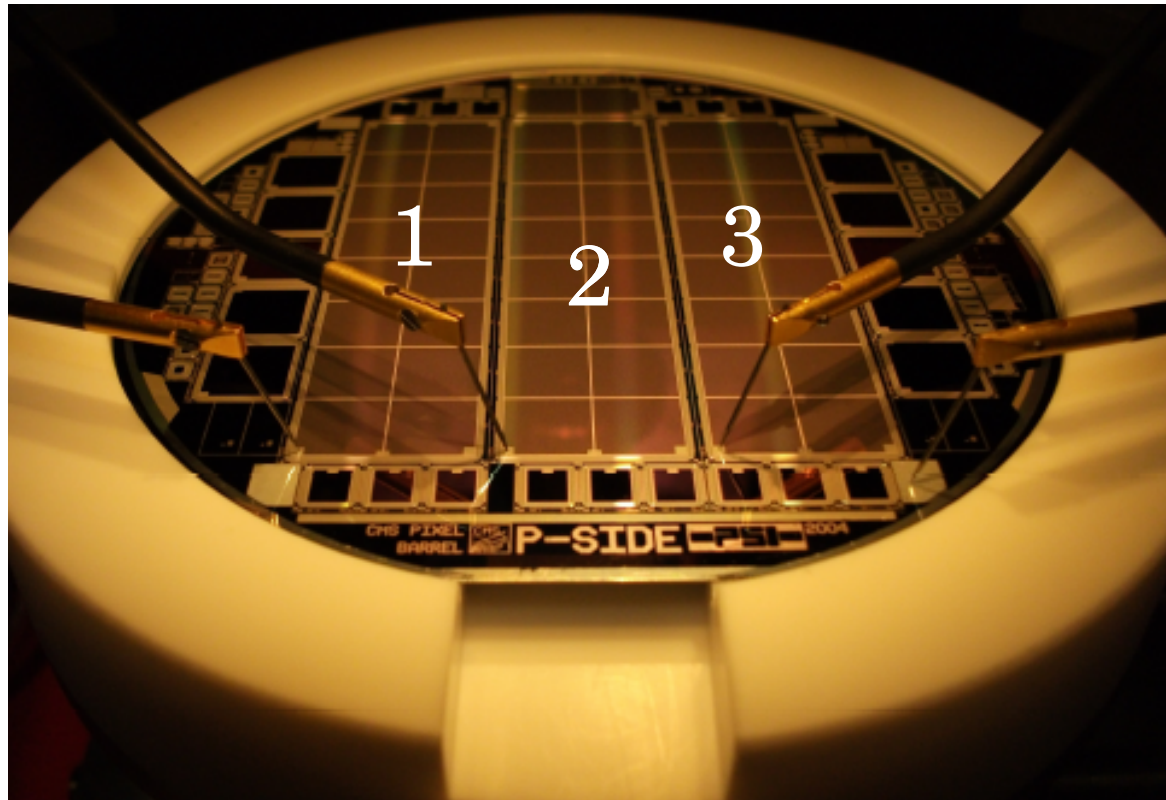
Chip203, $T = -15^\circ\text{C}$, $\text{Thr} = 35 \text{ Vcal}$



Leakage current: $700 \mu\text{A}$

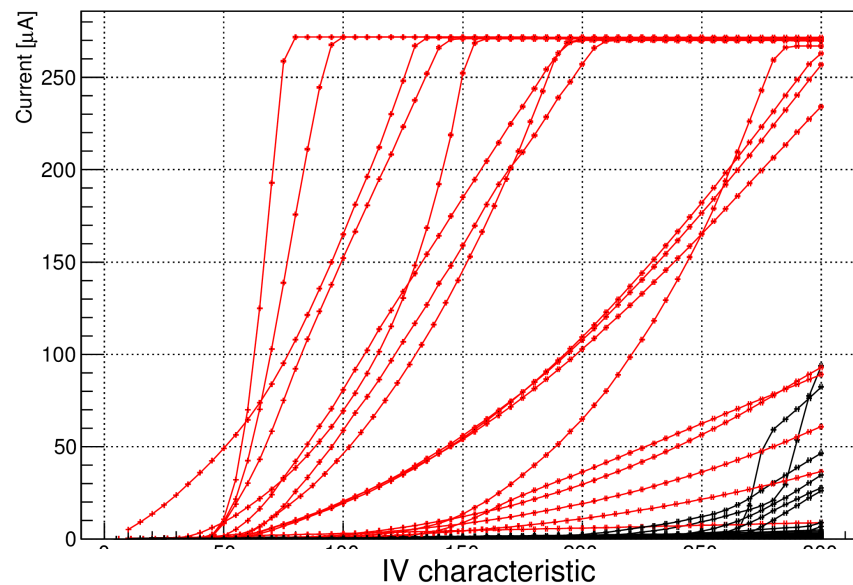
IV/CV Measurements of the remaining Wafers

2 Batches of 25 Wafers each



Current-Voltage (IV)

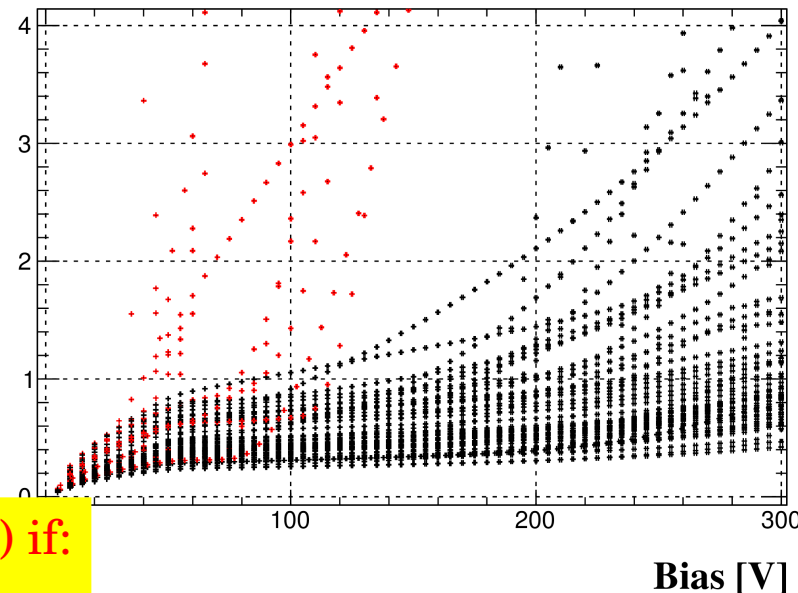
IV characteristic



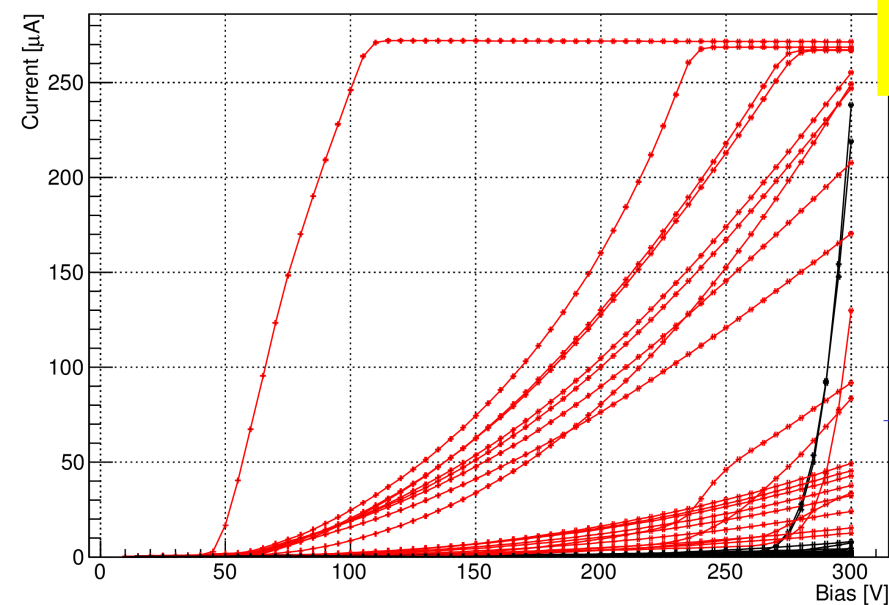
Batch: 322310

Zoom in

Current [μA]



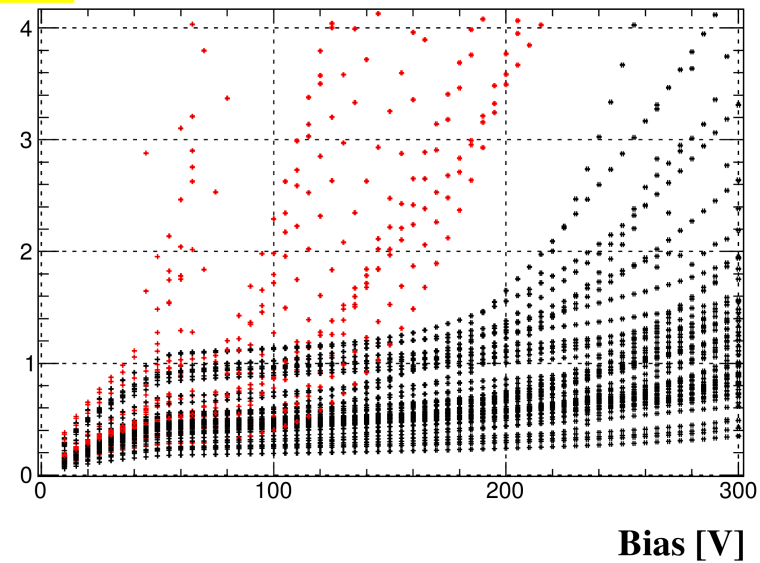
Bad Sensors (red) if:
 $I(150V) > 2 \mu A$
 $I(150V)/I(100V) > 2$



Batch: 322311

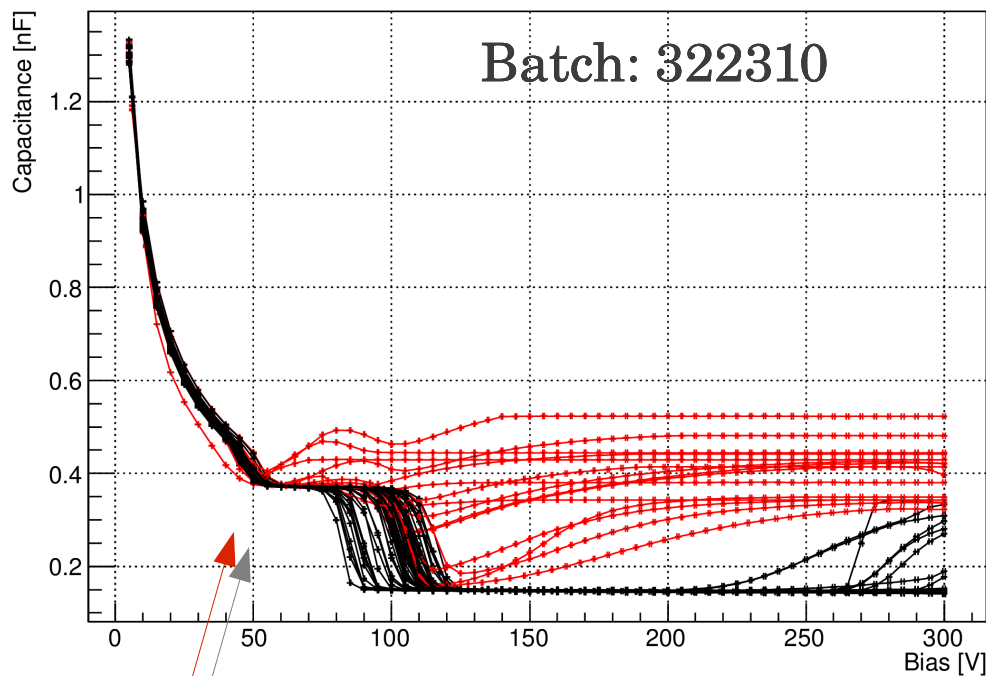
Zoom in

Current [μA]



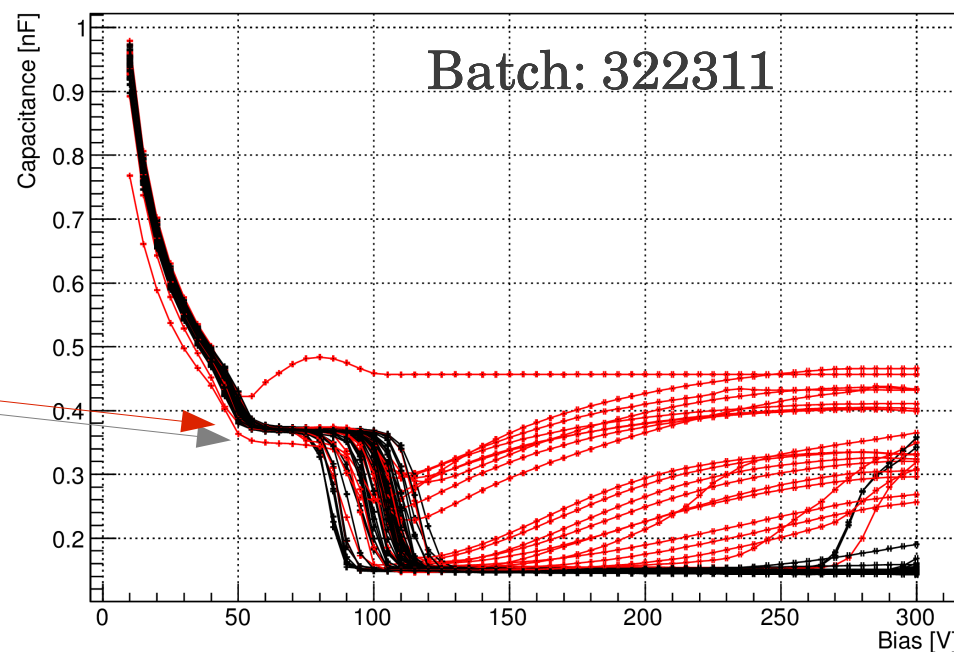
Capacitance-Voltage (CV)

CV characteristic



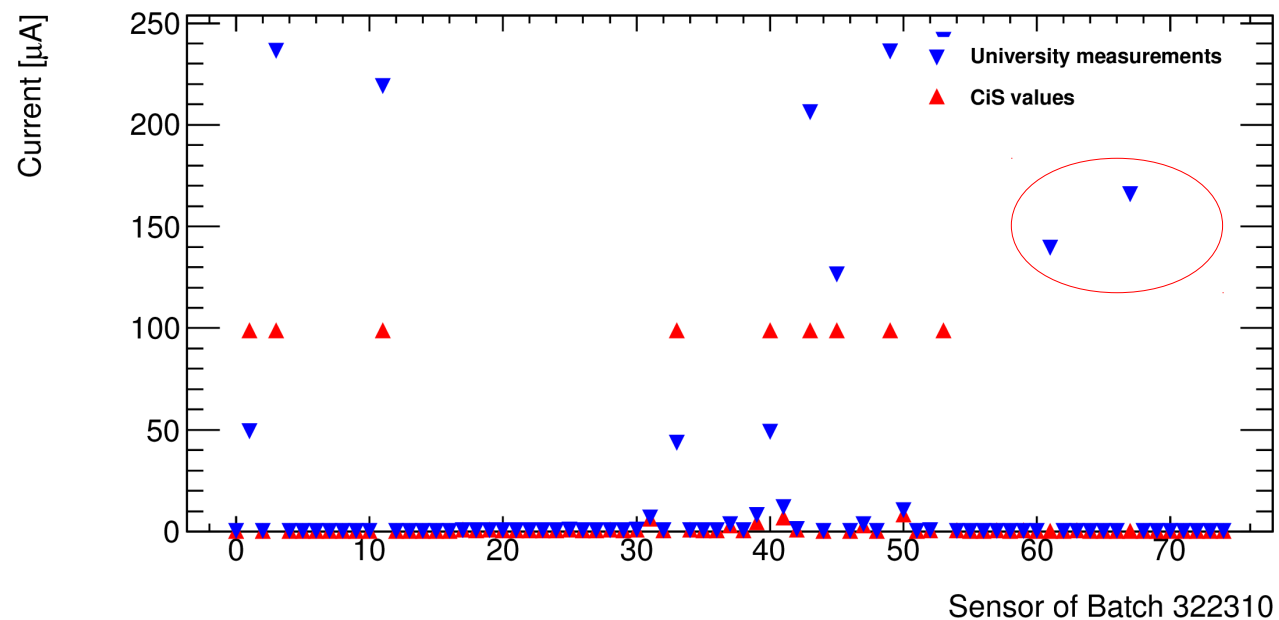
Depletion Voltage ~ 50V

CV characteristic



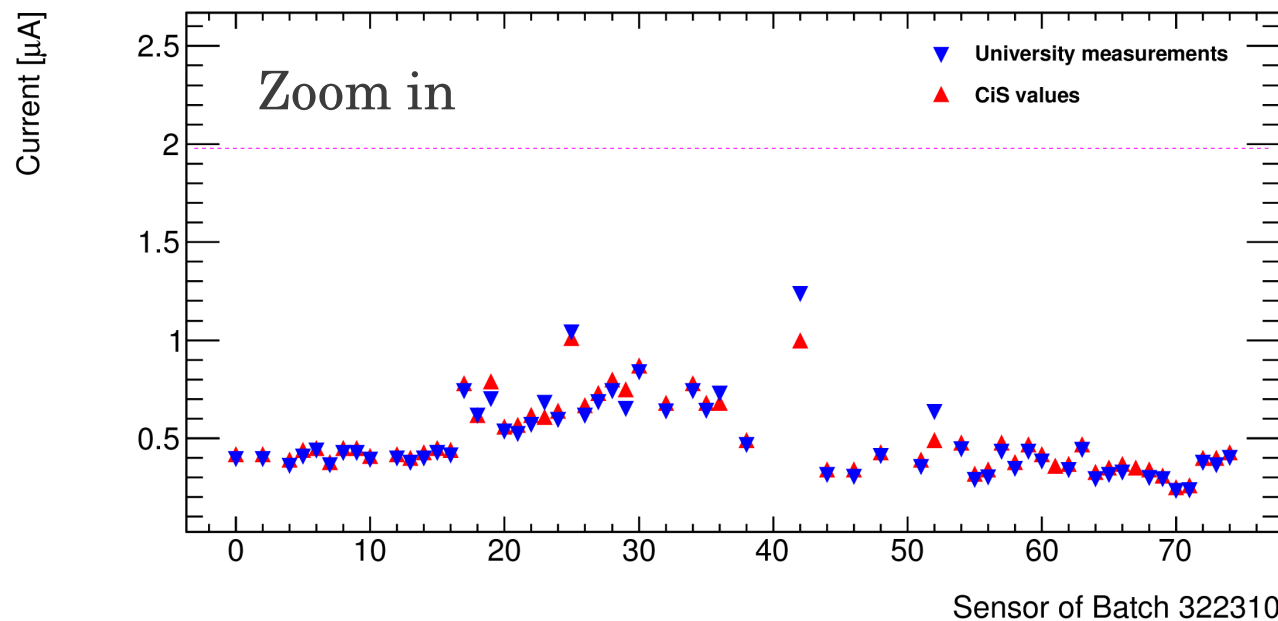
Comparisons with CiS

(Batch: 322310)



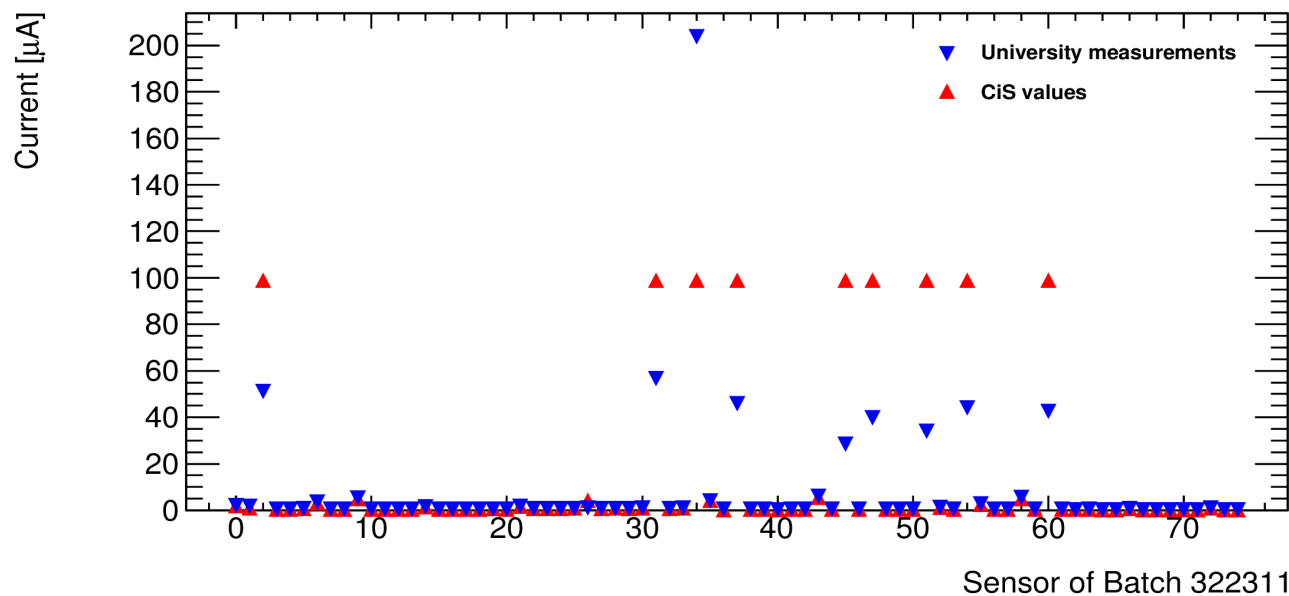
$I[\mu\text{A}]$ measured at 150V
scaled to $T=20^\circ$

Bad Sensors if:
 $I(150\text{V}) > 2 \mu\text{A}$



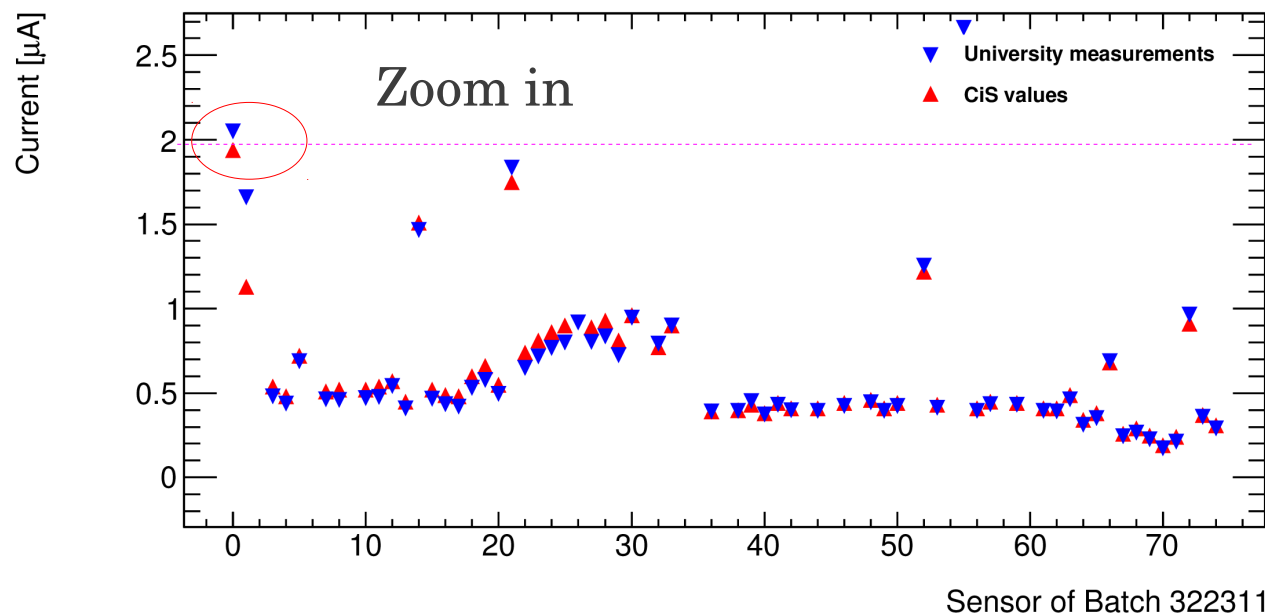
Comparisons with CiS

(Batch: 322311)



$I[\mu\text{A}]$ measured at 150V
scaled to $T=20^\circ$

Bad Sensors if:
 $I(150\text{V}) > 2 \mu\text{A}$

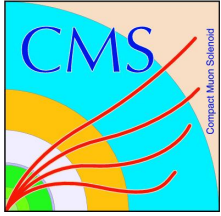


Conclusions

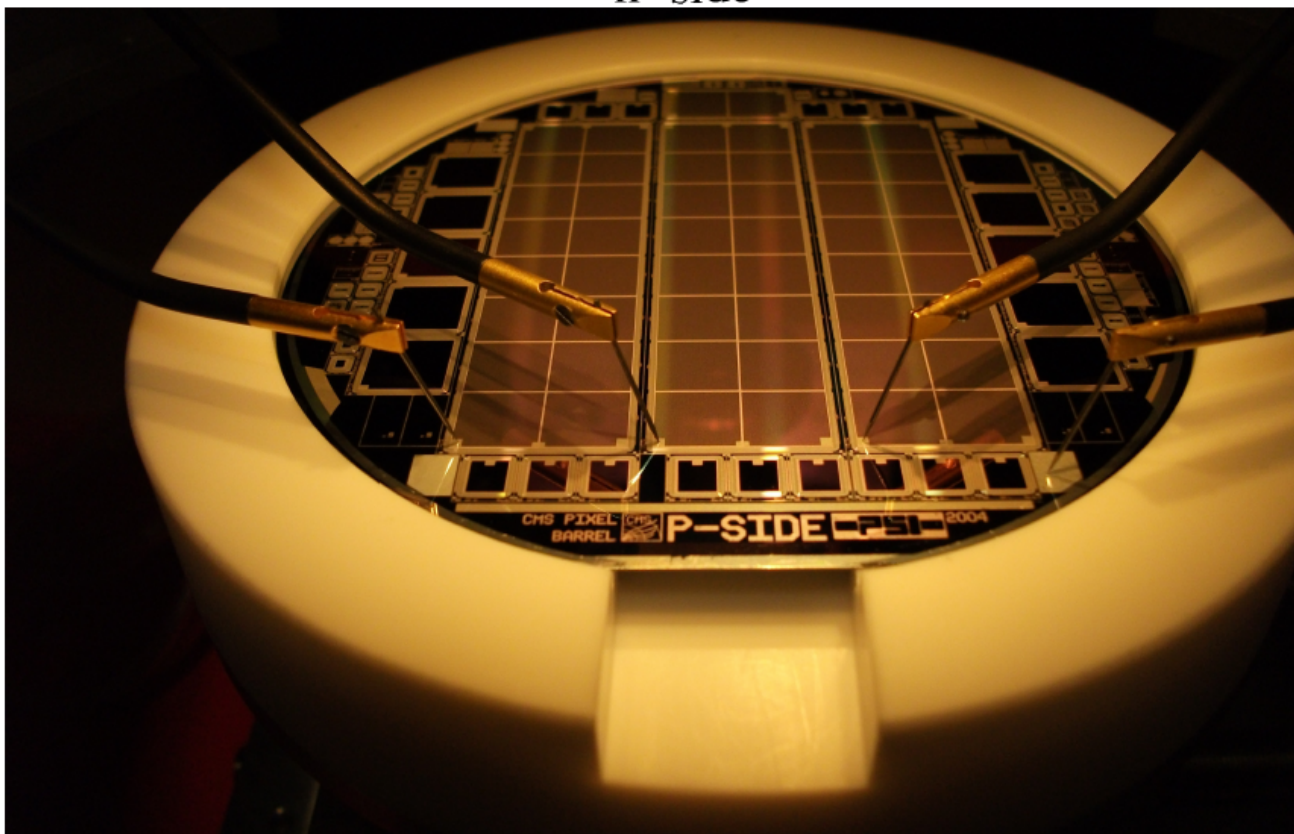
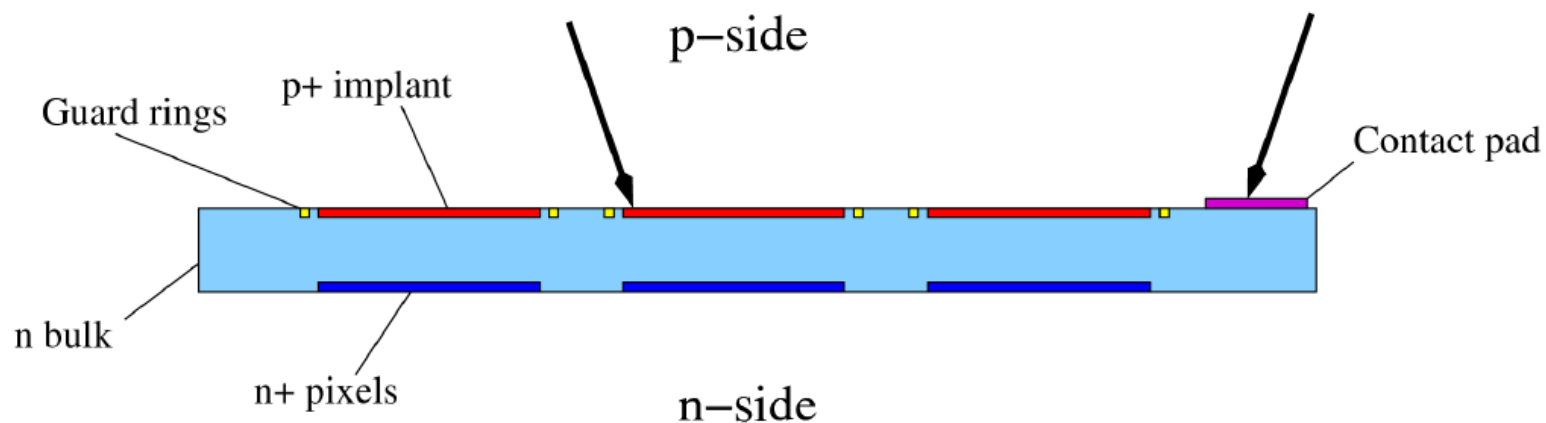
- Results from irradiated Chips are similar to un-irradiated Chip39 ($\sim 50\text{e}/\text{VCAL}$)
- Deviations of $\sim 3.5\%$ in calibration at different threshold and temperature. Large differences in offset (p_0) due to extrapolation.
- Our IV/CV measurements are in good agreement with those of CiS
- All 150 Sensors have been measured $\rightarrow$ They are ready to be sent to PakTech



Backup



Measurement Setup



Measurement Setup

- Temperature sensor
- Picoammeter
- Bias source
- LCR meter
- Teflon chuck
- Microscope

